Benjamin Damilano

List of Publications by Year
in descending order

240 papers	4,980 citations	87888 38 h-index	128289 60 g-index
241 all docs	241 docs citations	241 times ranked	3497 citing authors

#	Article	IF	Citations
1	Combination of selective area sublimation of p-GaN and regrowth of AlGaN for the co-integration of enhancement mode and depletion mode high electron mobility transistors. Solid-State Electronics, 2022, 188, 108210.	1.4	5
2	Les nouvelles diodes Ã©lectroluminescentes pour lâ€™Ã©mission UV. , 2022, , 16-21.	0.1	0
3	Influence of surface roughness on the lasing characteristics of optically pumped thin-film GaN microdisks. Optics Letters, 2022, 47, 1521.	3.3	7
4	Light Polarization in Tunnel Junction Injected UV Lightâ€Emitting Diodes. Physica Status Solidi (A) Applications and Materials Science, 2022, 219, 2200055.	1.8	0
5	Porous Nitride Light-Emitting Diodes. ACS Photonics, 2022, 9, 1256-1263.	6.6	5
6	Selective sublimation of GaN and regrowth of AlGaN to co-integrate enhancement mode and depletion mode high electron mobility transistors. Journal of Crystal Growth, 2022, , 126779.	1.5	0
7	Comparison of lasing characteristics of GaN microdisks with different structures. Journal Physics D: Applied Physics, 2022, 55, 355107.	2.8	2
8	Preferential sublimation along threading dislocations in InGaN/GaN single quantum well for improved photoluminescence. Journal of Applied Physics, 2022, 132, 035302.	2.5	1
9	Complexity of the dipolar exciton Mott transition in GaN/(AlGa)N nanostructures. Physical Review B, 2021, 103, .	3.2	7
10	Employing Cathodoluminescence for Nanothermometry and Thermal Transport Measurements in Semiconductor Nanowires. ACS Nano, 2021, 15, 11385-11395.	14.6	13
11	Broadband decoupling of intensity and polarization with vectorial Fourier metasurfaces. Nature Communications, 2021, 12, 3631.	12.8	50
12	Whispering-gallery mode InGaN microdisks on GaN substrates. Optics Express, 2021, 29, 21280.	3.4	6
13	Mapping of the electrostatic potentials in MOCVD and hybrid GaN tunnel junctions for InGaN/GaN blue emitting light emitting diodes by off-axis electron holography correlated with structural, chemical, and optoelectronic characterization. Journal of Applied Physics, 2021, 130, .	2.5	4
14	Bandwidth-unlimited polarization-maintaining metasurfaces. Science Advances, 2021, 7, .	10.3	52
15	Selective GaN sublimation and local area regrowth for co-integration of enhancement mode and depletion mode Al(Ga)N/GaN high electron mobility transistors. Semiconductor Science and Technology, 2021, 36, 024001.	2.0	3
16	Full InGaN red light emitting diodes. Journal of Applied Physics, 2020, 128, .	2.5	55
17	Cathodoluminescence and electrical study of vertical GaN-on-GaN Schottky diodes with dislocation clusters. Journal of Crystal Growth, 2020, 552, 125911.	1.5	4
18	Blue to yellow emission from (Ga,In)/GaN quantum wells grown on pixelated silicon substrate. Scientific Reports, 2020, 10, 18919.	3.3	1

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19	Analysis of low-threshold optically pumped III-nitride microdisk lasers. Applied Physics Letters, 2020, 117, .	3.3	14
20	High temperature electrical transport properties of MBE-grown Mg-doped GaN and AlGaN materials. Journal of Applied Physics, 2020, 128, .	2.5	5
21	Effect of AlGaN interlayer on the GaN/InGaN/GaN/AlGaN multi-quantum wells structural properties toward red light emission. Journal of Applied Physics, 2020, 128, .	2.5	10
22	Wetting-Layer-Free AlGaN Quantum Dots for Ultraviolet Emitters. ACS Applied Nano Materials, 2020, 3, 4054-4060.	5.0	0
23	Lasing up to 380â€‰K in a sublimated GaN nanowire. Applied Physics Letters, 2020, 116, .	3.3	13
24	Ptychography retrieval of fully polarized holograms from geometric-phase metasurfaces. Nature Communications, 2020, 11, 2651.	12.8	136
25	Multi-microscopy nanoscale characterization of the doping profile in a hybrid Mg/Ge-doped tunnel junction. Nanotechnology, 2020, 31, 465706.	2.6	6
26	InGaN islands and thin films grown on epitaxial graphene. Nanotechnology, 2020, 31, 405601.	2.6	3
27	Influence of the reactor environment on the selective area thermal etching of GaN nanohole arrays. Scientific Reports, 2020, 10, 5642.	3.3	7
28	Monolithic integration of ultraviolet microdisk lasers into photonic circuits in a III-nitride-on-silicon platform. Optics Letters, 2020, 45, 4276.	3.3	13
29	Printing polarization and phase at the optical diffraction limit: near- and far-field optical encryption. Nanophotonics, 2020, 10, 697-704.	6.0	19
30	Revealing topological phase in Pancharatnamâ€“Berry metasurfaces using mesoscopic electrodynamics. Nanophotonics, 2020, 9, 4711-4718.	6.0	7
31	Trapping Dipolar Exciton Fluids in GaN/(AlGa)N Nanostructures. Nano Letters, 2019, 19, 4911-4918.	9.1	9
32	Pendeo-epitaxy of GaN on SOI nano-pillars: Freestanding and relaxed GaN platelets on silicon with a reduced dislocation density. Journal of Crystal Growth, 2019, 526, 125235.	1.5	4
33	(Ga,In)N/GaN light emitting diodes with a tunnel junction and a rough n-contact layer grown by metalorganic chemical vapor deposition. AIP Advances, 2019, 9, 055101.	1.3	10
34	An Etchingâ€Free Approach Toward Largeâ€Scale Lightâ€Emitting Metasurfaces. Advanced Optical Materials, 2019, 7, 1801271.	7.3	37
35	Top-down fabrication of GaN nano-laser arrays by displacement Talbot lithography and selective area sublimation. Applied Physics Express, 2019, 12, 045007.	2.4	21
36	Subliming GaN into Ordered Nanowire Arrays for Ultraviolet and Visible Nanophotonics. ACS Photonics, 2019, 6, 3321-3330.	6.6	17

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37	Displacement Talbot lithography for nano-engineering of III-nitride materials. Microsystems and Nanoengineering, 2019, 5, 52.	7.0	33
38	Internal quantum efficiencies of AlGaN quantum dots grown by molecular beam epitaxy and emitting in the UVA to UVC ranges. Journal of Applied Physics, 2019, 126, .	2.5	17
39	Ge doped GaN and Al0.5Ga0.5N-based tunnel junctions on top of visible and UV light emitting diodes. Journal of Applied Physics, 2019, 126, .	2.5	24
40	Demonstration of critical coupling in an active III-nitride microdisk photonic circuit on silicon. Scientific Reports, 2019, 9, 18095.	3.3	11
41	III-nitride on silicon electrically injected microrings for nanophotonic circuits. Optics Express, 2019, 27, 11800.	3.4	20
42	Semiconductors Meta-Optics: Fabrication and Applications. , 2019, , .		0
43	Towards III-nitride on silicon active photonic circuits. , 2019, , .		0
44	Photoluminescence properties of (Al,Ga)N nanostructures grown on Al0.5Ga0.5N (0001). Superlattices and Microstructures, 2018, 114, 161-168.	3.1	6
45	Mesoporous GaN Made by Selective Area Sublimation for Efficient Light Emission on Si Substrate. Physica Status Solidi (B): Basic Research, 2018, 255, 1700392.	1.5	6
46	Crack Statististics and Stress Analysis of Thick GaN on Patterned Silicon Substrate. Physica Status Solidi (B): Basic Research, 2018, 255, 1700399.	1.5	3
47	Internal quantum efficiency in polar and semipolar (11â€“22) InxGa1-xN/InyGa1-yN quantum wells emitting from blue to red. Superlattices and Microstructures, 2018, 113, 129-134.	3.1	3
48	AlGaN/GaN/AlGaN DHâ€HEMTs Grown on a Patterned Silicon Substrate. Physica Status Solidi (A) Applications and Materials Science, 2018, 215, 1700642.	1.8	6
49	Enhanced excitonic emission efficiency in porous GaN. Scientific Reports, 2018, 8, 15767.	3.3	12
50	UVA and UVB light emitting diodes with Al_{<i>y</i>}Ga_{1â^'<i>y</i>}N quantum dot active regions covering the 305â€“335 nm range. Semiconductor Science and Technology, 2018, 33, 075007.	2.0	7
51	Optical and Thermal Performances of (Ga,In)N/GaN Light Emitting Diodes Transferred on a Flexible Tape. IEEE Photonics Technology Letters, 2018, 30, 1567-1570.	2.5	4
52	Blue Microlasers Integrated on a Photonic Platform on Silicon. ACS Photonics, 2018, 5, 3643-3648.	6.6	32
53	Internal quantum efficiency and Auger recombination in green, yellow and red InGaN-based light emitters grown along the polar direction. Superlattices and Microstructures, 2017, 103, 245-251.	3.1	23
54	Optical properties of InxGa1â^'xN/GaN quantum-disks obtained by selective area sublimation. Journal of Crystal Growth, 2017, 477, 262-266.	1.5	10

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55	Effect of the growth temperature and nitrogen precursor on the structural and electrical transport properties of SmN thin films. MRS Advances, 2017, 2, 165-171.	0.9	1
56	High Temperature Annealing of MBE-grown Mg-doped GaN. Journal of Physics: Conference Series, 2017, 864, 012018.	0.4	2
57	The microstructure, local indium composition and photoluminescence in greenâ€emitting InGaN/GaN quantum wells. Journal of Microscopy, 2017, 268, 305-312.	1.8	3
58	Photo-induced droop in blue to red light emitting InGaN/GaN single quantum wells structures. Journal of Applied Physics, 2017, 122, .	2.5	17
59	Epitaxial GdN/SmN-based superlattices grown by molecular beam epitaxy. MRS Advances, 2017, 2, 189-194.	0.9	1
60	Influence of the heterostructure design on the optical properties of GaN and Al0.1Ga0.9N quantum dots for ultraviolet emission. Journal of Applied Physics, 2017, 122, .	2.5	14
61	Photoluminescence properties of porous GaN and (Ga,In)N/GaN single quantum well made by selective area sublimation. Optics Express, 2017, 25, 33243.	3.4	15
62	Investigation of Al_yGa_{1âˆ’} _yN/Al_{0.5}Ga_{0.5}N quantum dot properties for the design of ultraviolet emitters. Japanese Journal of Applied Physics, 2016, 55, 05FG06.	1.5	13
63	III-Nitride-on-silicon microdisk lasers from the blue to the deep ultra-violet. Applied Physics Letters, 2016, 109, .	3.3	38
64	Auger effect in yellow light emitters based on InGaNâ€“AlGaNâ€“GaN quantum wells. Japanese Journal of Applied Physics, 2016, 55, 05FG10.	1.5	7
65	AlN interlayer to improve the epitaxial growth of SmN on GaN (0001). Journal of Crystal Growth, 2016, 450, 22-27.	1.5	5
66	High temperature electrical transport study of Si-doped AlN. Superlattices and Microstructures, 2016, 98, 253-258.	3.1	10
67	Temperature-Induced Four-Fold-on-Six-Fold Symmetric Heteroepitaxy, Rocksalt SmN on Hexagonal AlN. Crystal Growth and Design, 2016, 16, 6454-6460.	3.0	7
68	Impact of the Bending on the Electroluminescence of Flexible InGaN/GaN Light-Emitting Diodes. IEEE Photonics Technology Letters, 2016, 28, 1661-1664.	2.5	6
69	First Power Performance Demonstration of Flexible AlGaN/GaN High Electron Mobility Transistor. IEEE Electron Device Letters, 2016, 37, 553-555.	3.9	24
70	Selective Area Sublimation: A Simple Top-down Route for GaN-Based Nanowire Fabrication. Nano Letters, 2016, 16, 1863-1868.	9.1	48
71	Ultraviolet light emitting diodes using III-N quantum dots. Materials Science in Semiconductor Processing, 2016, 55, 95-101.	4.0	13
72	Optimized In composition and quantum well thickness for yellow-emitting (Ga,In)N/GaN multiple quantum wells. Journal of Crystal Growth, 2016, 434, 25-29.	1.5	6

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73	GaN films and GaN/AlGaN quantum wells grown by plasma assisted molecular beam epitaxy using a high density radical source. Journal of Crystal Growth, 2016, 433, 165-171.	1.5	6
74	Growth of nitrideâ€based light emitting diodes with a highâ€reflectivity distributed Bragg reflector on mesaâ€patterned silicon substrate. Physica Status Solidi (A) Applications and Materials Science, 2015, 212, 2297-2301.	1.8	9
75	Formation of GaN quantum dots by molecular beam epitaxy using NH3 as nitrogen source. Journal of Applied Physics, 2015, 118, .	2.5	29
76	Optical properties and structural investigations of (11-22)-oriented GaN/Al0.5Ga0.5N quantum wells grown by molecular beam epitaxy. Journal of Applied Physics, 2015, 118, 024303.	2.5	2
77	Internal quantum efficiency in yellow-amber light emitting AlGaN-InGaN-GaN heterostructures. Applied Physics Letters, 2015, 107, .	3.3	36
78	Optical properties of small GaN-Al0.5Ga0.5N quantum dots grown on (11-22) GaN templates. , 2015, , .		0
79	III-Nitride quantum dot based light emitting diodes for UV emission. , 2015, , .		0
80	Optical properties of Al0.5Ga0.5N/GaN polar quantum dots and UV LEDs made of them. , 2015, , .		0
81	Highly resistive epitaxial Mg-doped GdN thin films. Applied Physics Letters, 2015, 106, .	3.3	18
82	Photoluminescence behavior of amber light emitting GaInN-GaN heterostructures. Proceedings of SPIE, 2015, , .	0.8	0
83	Strain-compensated (Ga,In)N/(Al,Ga)N/GaN multiple quantum wells for improved yellow/amber light emission. Applied Physics Letters, 2015, 106, .	3.3	45
84	Yellowâ€“red emission from (Ga,In)N heterostructures. Journal Physics D: Applied Physics, 2015, 48, 403001.	2.8	78
85	Polar and semipolar GaN/Al_{0.5}Ga_{0.5}N nanostructures for UV light emitters. Semiconductor Science and Technology, 2014, 29, 084001.	2.0	30
86	AlGaN/GaN Nanostructures for UV Light Emitting Diodes. , 2014, , .		1
87	GaN-based heterostructures grown on ZnO substrates: from polarity control to the fabrication of blue LEDs. , 2014, , .		0
88	Stark effect in ensembles of polar (0001) Al0.5Ga0.5N/GaN quantum dots and comparison with semipolar (11â˜’22) ones. Journal of Applied Physics, 2014, 116, 034308.	2.5	15
89	Growth of GaN nanostructures with polar and semipolar orientations for the fabrication of UV LEDs. , 2014, , .		1
90	Capping green emitting (Ga,In)N quantum wells with (Al,Ga)N: impact on structural and optical properties. Semiconductor Science and Technology, 2014, 29, 035016.	2.0	9

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91	Monolithic white light emitting diodes using a (Ga,In)N-based light converter. , 2014, , .		1
92	The universal photoluminescence behaviour of yellow light emitting (Ga,In)N/GaN heterostructures. Superlattices and Microstructures, 2014, 76, 9-15.	3.1	8
93	Molecular beam epitaxy of ferromagnetic epitaxial GdN thin films. Journal of Crystal Growth, 2014, 404, 146-151.	1.5	18
94	Ultra-violet GaN/Al0.5Ga0.5N quantum dot based light emitting diodes. Journal of Crystal Growth, 2013, 363, 282-286.	1.5	44
95	Dependence of the Mg-related acceptor ionization energy with the acceptor concentration in p-type GaN layers grown by molecular beam epitaxy. Applied Physics Letters, 2013, 103, .	3.3	96
96	Excitons in nitride heterostructures: From zero- to one-dimensional behavior. Physical Review B, 2013, 88, .	3.2	50
97	Stress distribution of 12 Î¼m thick crack free continuous GaN on patterned Si(110) substrate. Physica Status Solidi C: Current Topics in Solid State Physics, 2013, 10, 425-428.	0.8	12
98	GaN doped with berylliumâ€"An effective light converter for white light emitting diodes. Applied Physics Letters, 2013, 103, .	3.3	23
99	Imaging and counting threading dislocations in c-oriented epitaxial GaN layers. Semiconductor Science and Technology, 2013, 28, 035006.	2.0	32
100	AlGaN/GaN HEMTs with an InGaN backâ€barrier grown by ammoniaâ€assisted molecular beam epitaxy. Physica Status Solidi (A) Applications and Materials Science, 2013, 210, 480-483.	1.8	11
101	Built-in electric field and radiative efficiency of polar (0001) and semipolar (11â€"22) Al[sub 0.5]Ga[sub 0.5]Nâˆ•GaN quantum dots. , 2013, , .		1
102	Measurement of the effect of plasmon gas oscillation on the dielectric properties of p- and n-doped AlxGa1â^'xN films using infrared spectroscopy. Journal of Applied Physics, 2013, 114, 053505.	2.5	10
103	Built-in electric field in ZnO based semipolar quantum wells grown on (101Â¯2) ZnO substrates. Applied Physics Letters, 2013, 103, .	3.3	11
104	Role of magnetic polarons in ferromagnetic GdN. Physical Review B, 2013, 87, .	3.2	40
105	Metal Organic Vapor Phase Epitaxy of Monolithic Two-Color Light-Emitting Diodes Using an InGaN-Based Light Converter. Applied Physics Express, 2013, 6, 092105.	2.4	14
106	Blue Light-Emitting Diodes Grown on ZnO Substrates. Applied Physics Express, 2013, 6, 042101.	2.4	14
107	AlGaN-Based Light Emitting Diodes Using Self-Assembled GaN Quantum Dots for Ultraviolet Emission. Japanese Journal of Applied Physics, 2013, 52, 08JG01.	1.5	16
108	Current transport through an nâ€doped, nearly lattice matched GaN/AlInN/GaN heterostructure. Physica Status Solidi C: Current Topics in Solid State Physics, 2012, 9, 931-933.	0.8	3

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109	Growth optimization and characterization of lattice-matched Al0.82In0.18N optical confinement layer for edge emitting nitride laser diodes. Journal of Crystal Growth, 2012, 338, 20-29.	1.5	10
110	Color control in monolithic white light emitting diodes using a (Ga,In)N/GaN multiple quantum well light converter. Physica Status Solidi (A) Applications and Materials Science, 2012, 209, 465-468.	1.8	5
111	Control of polarized emission from selectively etched GaN/AlN quantum dot ensembles on Si(111). Physica Status Solidi C: Current Topics in Solid State Physics, 2012, 9, 1011-1015.	0.8	0
112	GaN/Al0.5Ga0.5N (11-22) semipolar nanostructures: A way to get high luminescence efficiency in the near ultraviolet range. Journal of Applied Physics, 2011, 110, .	2.5	23
113	Selective control of polarized emission from patterned GaN/AlN quantum dot ensembles on Si(111). Applied Physics Letters, 2011, 98, 061903.	3.3	4
114	Study of the growth mechanisms of GaN/(Al, Ga)N quantum dots: Correlation between structural and optical properties. Journal of Applied Physics, 2011, 109, 053514.	2.5	11
115	Excitation-dependent Polarized Emission from GaNâ^•AlN Quantum Dot Ensembles under In-plane Uniaxial Stresses. AIP Conference Proceedings, 2011, , .	0.4	1
116	Polarized light from excitonic recombination in selectively etched GaN/AlN quantum dot ensembles on Si(111). Journal Physics D: Applied Physics, 2011, 44, 505101.	2.8	5
117	Growth of GaN based structures on Si(110) by molecular beam epitaxy. Journal of Crystal Growth, 2010, 312, 2683-2688.	1.5	25
118	Current Spreading Efficiency and Fermi Level Pinning in GaInNAsâ€“GaAs Quantum-Well Laser Diodes. IEEE Journal of Quantum Electronics, 2010, 46, 1058-1065.	1.9	3
119	Asymmetric barrier composition GaN/(Ga,In)N/(Al,Ga)N quantum wells for yellow emission. Physica Status Solidi C: Current Topics in Solid State Physics, 2010, 7, 2130-2132.	0.8	1
120	Blue-green and white color tuning of monolithic light emitting diodes. Journal of Applied Physics, 2010, 108, 073115.	2.5	47
121	External efficiency and carrier loss mechanisms in InAs/GaInNAs quantum dot light-emitting diodes. Journal of Applied Physics, 2010, 108, 033104.	2.5	1
122	Polarized emission from GaN/AlN quantum dots subject to uniaxial thermal interfacial stresses. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2010, 28, C5E25-C5E34.	1.2	5
123	Electronic and optical properties of GaN/AlN quantum dots on Si(111) subject to in-plane uniaxial stresses and variable excitation. Journal of Applied Physics, 2010, 108, 083510.	2.5	6
124	Optical and Structural Properties of an Eu Implanted Gallium Nitride Quantum Dots/Aluminium Nitride Superlattice. Journal of Nanoscience and Nanotechnology, 2010, 10, 2473-2478.	0.9	3
125	Infrared detectors based on InGaAsNâ^•GaAs intersubband transitions. Applied Physics Letters, 2009, 94, 022103.	3.3	4
126	Tailoring the shape of GaN/AlxGa1â^'xN nanostructures to extend their luminescence in the visible range. Journal of Applied Physics, 2009, 105, 033519.	2.5	30

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127	GaN/Al_{0.5}Ga_{0.5}N quantum dots and quantum dashes. Physica Status Solidi (B): Basic Research, 2009, 246, 842-845.	1.5	2
128	AlGaN/GaN high electron mobility transistor grown by molecular beam epitaxy on Si(110): comparisons with Si(111) and Si(001). Physica Status Solidi C: Current Topics in Solid State Physics, 2009, 6, S1020.	0.8	13
129	Perturbing GaN/AlN quantum dots with uniaxial stressors. Physica Status Solidi C: Current Topics in Solid State Physics, 2009, 6, 1432-1435.	0.8	4
130	Electroluminescence analysis of 1.3-1.5 Î¼m InAs quantum dot LEDs with (Ga,In)(N,As) capping layers. Physica Status Solidi C: Current Topics in Solid State Physics, 2009, 6, 1424-1427.	0.8	1
131	Signature of monolayer and bilayer fluctuations in the width of (Al,Ga)N/GaN quantum wells. Physical Review B, 2009, 79, .	3.2	9
132	Blue-light emission from GaNâˆ•Al0.5Ga0.5N quantum dots. Applied Physics Letters, 2008, 92, 051911.	3.3	40
133	Demonstration of AlGaN/GaN High-Electron-Mobility Transistors Grown by Molecular Beam Epitaxy on Si(110). IEEE Electron Device Letters, 2008, 29, 1187-1189.	3.9	44
134	Monolithic white light emitting diodes using a (Ga,In)N/GaN multiple quantum well light converter. Applied Physics Letters, 2008, 93, 101117.	3.3	29
135	Optimum annealing temperature versus nitrogen composition in InAs/(Ga, In) (N, As) quantum dots. Semiconductor Science and Technology, 2008, 23, 035020.	2.0	1
136	Analysis of the characteristic temperatures of (Ga,In)(N,As)/GaAs laser diodes. Journal Physics D: Applied Physics, 2008, 41, 155102.	2.8	4
137	High doping level in Mg-doped GaN layers grown at low temperature. Journal of Applied Physics, 2008, 103, 013110.	2.5	44
138	Effect of uniaxial stress on the polarization of light emitted from<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:mrow><mml:mi mathvariant="normal">Ga</mml:mi><mml:mi mathvariant="normal">N</mml:mi><mml:mo>âˆ•</mml:mo><mml:mi mathvariant="normal">Al</mml:mi><mml:mi mathvariant="normal">N</mml:mi></mml:mrow></mml:math>quantum dots grown on Si(111). Physical	3.2	10
139	Annealing effects on InGaAsNâˆ•GaAs quantum wells analyzed using thermally detected optical absorption and ten band kâˆ™p calculations. Journal of Applied Physics, 2007, 101, 073510.	2.5	3
140	Microcrack-induced strain relief inGaNâˆ•AlNquantum dots grown on Si(111). Physical Review B, 2007, 75, .	3.2	20
141	Exciton dissociation and hole escape in the thermal photoluminescence quenching of(Ga,In)(N,As)quantum wells. Physical Review B, 2007, 75, .	3.2	25
142	Blue-shift mechanisms in annealed(Ga,In)(N,As)âˆ•GaAsquantum wells. Physical Review B, 2007, 75, .	3.2	24
143	Optical determination of the effective wetting layer thickness and composition in<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:mrow><mml:mi mathvariant="normal">In</mml:mi><mml:mi mathvariant="normal">As</mml:mi><mml:mo>âˆ•</mml:mo><mml:mi mathvariant="normal">Ga</mml:mi><mml:mrow><mml:mo>(</mml:mo><mml:mi) Tj ETQq1 1 0.784314 rgBT /Overlock 10 Tf 50 87 Td mathvariant="normal"	3.2	33
144	Investigation of Non-Radiative Processes in InAs/(Ga,In)(N,As) Quantum Dots. Japanese Journal of Applied Physics, 2007, 46, L317-L319.	1.5	2

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145	Monolithic white light emitting diodes with a broad emission spectrum. Physica Status Solidi C: Current Topics in Solid State Physics, 2007, 4, 57-60.	0.8	7
146	Radiative lifetime in wurtzite GaN/AlN quantum dots. Physica Status Solidi C: Current Topics in Solid State Physics, 2007, 4, 183-186.	0.8	1
147	Radiative lifetime of a single electron-hole pair inGaNâˆ•AlNquantum dots. Physical Review B, 2006, 73, .	3.2	106
148	1.5 Âµm luminescence from InAs/GaxIn1â€"xNyAs1â€"y quantum dots grown on GaAs substrate. Physica Status Solidi C: Current Topics in Solid State Physics, 2006, 3, 3848-3851.	0.8	0
149	Optimization of InAs/(Ga,In)As quantum dots in view of efficient emission at 1.5 Âµm. Physica Status Solidi C: Current Topics in Solid State Physics, 2006, 3, 3979-3982.	0.8	2
150	Long wavelength emitting InAsâˆ•Ga0.85In0.15NxAs1âˆ'x quantum dots on GaAs substrate. Applied Physics Letters, 2006, 88, 231902.	3.3	23
151	Optimum indium composition for (Ga,In)(N,As)âˆ•GaAs quantum wells emitting beyond 1.5Î¼m. Applied Physics Letters, 2006, 88, 091111.	3.3	13
152	Light-ion beam for microelectronic applications. Nuclear Instruments & Methods in Physics Research B, 2005, 240, 265-270.	1.4	5
153	Surface morphology of AlN and size dispersion of GaN quantum dots. Journal of Crystal Growth, 2005, 274, 387-393.	1.5	11
154	Performance improvement of 1.52â€…[micro sign]m (Ga,In)(N,As)âˆ•GaAs quantum well lasers on GaAs substrates. Electronics Letters, 2005, 41, 595.	1.0	12
155	(Ga,In)(N,As)/GaAs quantum wells grown by molecular beam epitaxy for above 1.3 Î¼m low threshold lasers. , 2005, , .		0
156	InAs/In0.15Ga0.85As1âˆ'xNx quantum dots for 1.5 Î¼m laser applications. Materials Research Society Symposia Proceedings, 2005, 891, 1.	0.1	4
157	Growth and in situ annealing conditions for long-wavelength (Ga, In)(N, As)/GaAs lasers. Applied Physics Letters, 2005, 86, 071105.	3.3	16
158	Analysis of the room temperature performance of 1.3-1.52 Î¼m GaInNAs/GaAs LDs grown by MBE. , 2005, 5840, 72.		0
159	Influence of carrier localization on the performance of MBE grown GaInNAs/GaAs QW light emitting diodes and laser diodes. , 2005, 5840, 81.		4
160	Impact of N on the lasing characteristics of GaInNAsâˆ•GaAs quantum well lasers emitting from 1.29 to 1.52Î¼m. Applied Physics Letters, 2005, 87, 251109.	3.3	15
161	Room temperature performance of low threshold 1.34-1.44-/spl mu/m GaInNAs-GaAs quantum-well lasers grown by molecular beam epitaxy. IEEE Photonics Technology Letters, 2005, 17, 1142-1144.	2.5	4
162	Inhomogeneous broadening ofAlxGa1âˆ'xNâˆ•GaNquantum wells. Physical Review B, 2005, 71, .	3.2	42

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